

# GaAsP/GaP Yellow Chip ---TK0110HYN

## 1. Scope

- The specification applies to GaAsP LED chips.
- Type : TK0110HYN.

## 2. Structure

- GaAsP/GaP yellow LED chip.
- P/N mesa type.
- Electrode P (anode) side : Aluminum or Gold.
- Electrode N (cathode) side : Gold alloy.

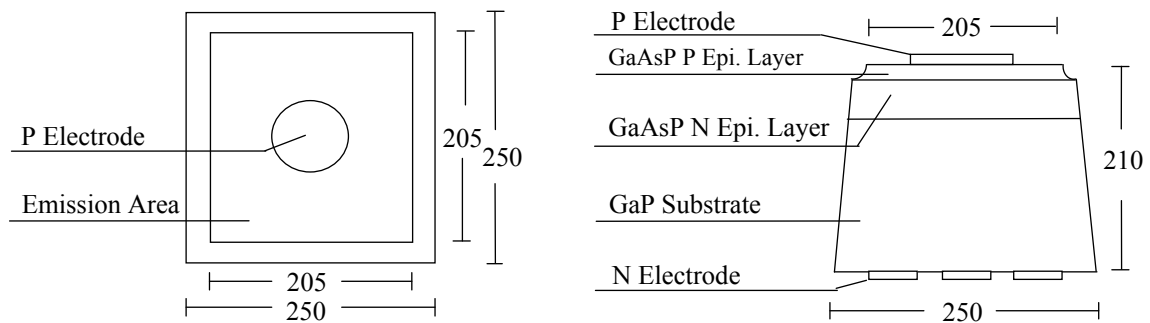
## 3. Size

- Chip size :  $250\mu\text{m} \times 250\mu\text{m}$
- Chip height :  $210\mu\text{m} \pm 30\mu\text{m}$
- Pattern drawing : per fig. 1

## 4. Electro-Optical Characteristics

( $T_a = +25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 20\text{mA}$		2.15	2.50	V
Reverse Current	$I_R$	$V_R = 5\text{V}$			10	$\mu\text{A}$
Luminous Intensity	$I_V$	$I_F = 20\text{mA}$	3.0	4.0		mcd
Wavelength	$\Delta p / \lambda d$	$I_F = 20\text{mA}$		583/585		nm
Spectrum Width of Half Value	$\Delta\lambda$	$I_F = 20\text{mA}$		32		nm



Unit :  $\mu\text{m}$

fig. 1

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## Electro-Optical Characteristics Curve

